Effect of sample size on the magnetic critical current density in nano-SiC doped MgB2 superconductors

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Effect of sample size on the magnetic critical current density in nano-SiC doped MgB$_2$ superconductors

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The effect of sample size on the critical current density and the flux pinning of pure and SiC doped MgB$_2$ bulk samples has been investigated. At high fields a systematic degradation of magnetic $J_c$ and $H_{ir}$ was observed as the sample size decreased. However, $J_c$ remarkably increased on decreasing the sample volume at low magnetic fields below 1 T. The SiC doped samples show less sample size effect than the pure samples, indicating a larger $n$ factor and therefore a stronger pinning effect due to SiC doping. $H_{ir}$ was observed to decrease as a logarithmic function of the sample volume, and the zero field $J_c$ can be fitted as an exponential decay function.

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The recent discovery of MgB$_2$ superconductors has attracted remarkable attention. It shows great potential for applications due to its relatively high transition temperature. Improving the critical current density ($J_c$) is one of the most important issues so far as applications are concerned. One of the best $J_c$ field performances has been reported recently for nano-SiC doped MgB$_2$ bulk and wires. Results show that SiC doped MgB$_2$ superconductors are one of the best candidates for high-field applications.

In contrast to the direct transport $J_c$ measurements used for tapes and wires, for bulk samples one has to calculate the magnetic $J_c$ from the dc magnetization using the Bean model. In our recent work we have shown that the magnetic $J_c$ strongly depends on the sample size. In contrast to the high-$T_c$ superconductor materials it was observed that in pure MgB$_2$ bulk samples $H_{ir}$ decreased as the sample volume decreased. Due to the dependence of $J_c$ on sample size, for a reliable comparison of $J_c$ values derived from magnetic measurements, sample size has to be carefully taken into account.

Some explanations have been presented to explain this behavior. Jin et al. suggested a linear dependence of the activation energy on the $J_c$ and gave an explanation for the $J_c$ dependence on the sample size. They proposed that in a cylindrical MgB$_2$ sample, vortices are remarkably rigid in small samples up to 1 mm long, while they behave as individual segments for longer samples. Horvat et al. qualitatively explain this phenomenon by considering the different coupling between the grains at different length scales. Very recently Qin et al. established a model to explain this effect. Based on this model, the magnetic $J_c$ depends on sample size as $J_c\propto R^{3n}$ where $R$ is the radius of a cylindrical sample and $n$ is the $n$ factor characterizing the $E-J$ curve $E=\frac{E_c(J/J_c)^n}{1-(1-a\beta)}$. They proposed that the low-$n$ factor at high magnetic fields is the reason for the significant sample size effect for pure MgB$_2$ superconductors.

As the nano-SiC doped sample exhibited much stronger flux pinning than the pure MgB$_2$, we intend to investigate the size effect in the strong pinning samples and compare them with pure MgB$_2$ samples. A detailed study with the aim to further understand the sample size effect in both pure and doped MgB$_2$ superconductor is presented in this paper.

Two groups of polycrystalline MgB$_2$ and MgB$_2$+10% SiC samples were synthesized from high-purity Mg and B and nano-SiC powders using the high isostatic pressure (HIP) method. The sample preparation details have been explained elsewhere. The magnetization was measured over a temperature range of 5 K to 30 K using a physical properties measurement system (PPMS, Quantum Design) in a time-varying magnetic field of sweep rate 50 Oe/s and amplitude 9 T. Bar-shaped samples were cut and dry polished from each pellet for magnetic measurements. The shiny polished surface was golden and black for the pure and doped samples, respectively. The sample volume was decreased about 75% through sawing and dry polishing after each measurement. To avoid any geometrical effect on the results, each dimension is reduced by a factor of about 0.35% (i.e., the ratio of $a:b:c$ remains constant) before each subsequent measurement.

The sample information is presented in Table I. The magnetic measurements were performed by applying the magnetic field parallel to the longest sample axis. The magnetic $J_c$ was calculated from the height $\Delta M$ of the magnetization loop ($M-H$) using the Bean model, where $J_c=20\Delta M/[a(1-a\beta)]$, where $a$ and $b$ are the dimensions of the sample perpendicular to the direction of the applied magnetic field with $a\leq b$. $J_c$ versus magnetic field was measured up to 8.5 T for all the samples at 5 K, 10 K, 20 K, and 30 K. $T_c$ was determined to be 38.6 K and 37.05 K for the pure and doped samples, respectively. A small bar shaped sample of the same size as sample 4 was directly cut from the same batch and given a $J_c$ measurement. No significant difference was found between the results for this sample and for sample 4, indicating that the repeated polishing and measurements had no effect on the samples.

The field dependence of $J_c$ for SiC doped and undoped MgB$_2$ samples at 5 K, 20 K, and 30 K for samples of different sizes are presented in Figs. 1(a) and 1(b), respectively. It can be clearly seen that in both doped and undoped samples the $J_c$ field performance strongly depends on the sample size. At high fields, $J_c$ significantly decreased as a function...
of the magnetic field as the sample size decreased. On the other hand, the low-field $J_c$ increased as the sample size decreased in both pure and doped samples. These changes in either low fields or in high fields are stronger in the lower-temperature regime.

Flux jumping was observed in both pure and doped samples but flux jumps occurred at higher fields for bigger samples. Flux jumping was also found to be less serious in the doped samples. For sample 1 flux jumping was observed up to 3.9 T for the doped sample, but in the pure sample flux jumping can be seen even at 5 T. Flux jumping also occurred in the pure samples 1 and 2 at 20 K, but no flux jumping was observed in the doped samples at 20 K.

The ratio of $J_{c1}/J_{c4}$ for samples 1 and 4 between 5 T and 8.5 T for both pure and doped samples at 5 K are presented in Fig. 2. For both samples the larger the sample, the higher the $J_{c1}/J_{c4}$ ratio. However, the sample size dependence is much more pronounced in the undoped sample. At 6.5 T and 5 K $J_{c4}$ is lower than $J_{c1}$ by a factor of 1.8 for the doped samples. However, under the same conditions, $J_{c4}$ is more than one order of magnitude lower than $J_{c1}$ in the pure samples. The $J_c$ field dependence of the doped samples at low magnetic fields and 20 K are shown in the inset of Fig. 2. As we can see, the zero-field $J_c$ increases as the sample size decreases. However, the differences between the $J_c$ values of all the samples are reduced by increasing the magnetic field. The $J_c$ field dependence curve of sample 1 crosses over the $J_c$ curves of the smaller samples at a magnetic field of about 1 T. The same behavior was also found in the pure samples.

The dependence of the irreversibility field $H_{irr}$ on the volume of pure and doped samples at 20 K is shown in a semi-logarithmic plot in Fig. 3. $H_{irr}$ was determined from $J_c$-$H$ curves using the criterion of 100 A/cm². Some points for the pure samples were extracted from our previous work. As we can see, $H_{irr}$ decreases logarithmically as the sample volume decreases. The irreversibility field $H_{irr}$ versus the sample volume is plotted in the inset with linear scaling, showing a gradual saturation behavior as the sample volume increases. Almost the same trend was found at other temperatures as well.

Figure 4 shows the dependence of the zero-field critical current ($J_{c0}$) on the sample volume of pure and doped samples at 20 K and 30 K. Some points for pure samples

<table>
<thead>
<tr>
<th>Sample</th>
<th>Undoped</th>
<th>Doped</th>
</tr>
</thead>
<tbody>
<tr>
<td>$a$ (mm)</td>
<td>$b$ (mm)</td>
<td>$c$ (mm)</td>
</tr>
<tr>
<td>1</td>
<td>1.07</td>
<td>3.27</td>
</tr>
<tr>
<td>2</td>
<td>0.7</td>
<td>2.12</td>
</tr>
<tr>
<td>3</td>
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<td>1.34</td>
</tr>
<tr>
<td>4</td>
<td>0.29</td>
<td>0.85</td>
</tr>
</tbody>
</table>

FIG. 1. (a) Magnetic $J_c$ field dependence of the MgB₂ + 10%SiC samples of different sizes (Table I) at 5 K, 20 K, and 30 K. (b) Magnetic $J_c$ field dependence of the pure MgB₂ samples of different sizes (Table I) at 5 K, 20 K, and 30 K.

FIG. 2. The ratio of $J_{c1}/J_{c4}$ between 5 T and 8.5 T for both pure and doped samples at 5 K. The $J_c$ field dependence of doped sample at low magnetic fields at 20 K is shown in the inset.
were extracted from our previous work. All \( J_{c0} \) values were normalized to the \( J_{c0} \) value of the biggest sample. Over all temperature ranges the smaller samples had a higher \( J_{c0} \). For pure samples the normalized \( J_{c0} \) increases slightly as the sample volume decreases down to 7 mm\(^3\), followed by a faster increase for smaller sample volumes. \( J_{c0} \) can also be very well scaled for both 20 K and 30 K with the same curve. However, for doped samples, \( J_{c0} \) increases more gradually than for the pure samples as the sample size decreases.

Moreover, the \( J_{c0} \) values for 20 K and 30 K cannot be scaled using the same curve. The difference between the normalized \( J_{c0} \) values for 20 K and 30 K is increased by decreasing the volume. The lower the temperature, the faster \( J_{c0} \) increases. The absolute value of \( J_{c0} \) versus the sample volume for pure and doped samples at 20 K is plotted on a logarithmic scale in the inset to Fig. 4. The curves can be fitted as an exponential decay function as is shown in the figure.

Based on the Qin et al. method we have plotted ln(\( J_{c} \)) versus ln(\( ab/(a+b) \)) for the doped samples at 20 K and at 3 T, 4 T, 5 T, and 6 T in Fig. 5. Similar curves at 5 K and 30 K for different magnetic fields are presented in the insets of this figure. The solid lines are the best linear fittings between ln(\( J_{c} \)) and ln(\( ab/(a+b) \)). The inverses of the slopes give the \( n \) factors. Calculated \( n \) factors for the SiC doped samples are shown in Fig. 6 at 5 K, 20 K, and 30 K. The \( n \) factors of pure samples extracted from our recent work\(^7\) are also included as open squares and open triangles for 5 K and 20 K, respectively. The solid lines are just guides to the eye.

As the \( n \) factor is the exponent characterizing the \( E - j \) curve \( E = E_c(j/j_c)^n \), a large \( n \) factor will lead to a sharp \( E - j \) curve. On the other hand, the \( n \) factor can be calculated as \( n = U_0/kT \), where \( U_0 \) is the energy scale for the current density dependent activation energy \( U(j) = U_0 \ln(j/j_c) \) with \( k \) the Boltzmann constant. Therefore a large \( n \) indicates a stronger pinning effect. Moreover, the dependence of the current density on the sample size has been derived to be \( j \propto R^{1/n} \), indicating that a large \( n \) will give rise to less sample size dependence. It can be seen from Fig. 6 that the \( n \) factors of the doped sample are much higher than those of the pure samples, indicating that strong pinning centers have been introduced into the MgB\(_2\) samples by means of SiC doping. Figure 6 also explains the observed lesser sample size effect in the SiC doped samples shown in Figs. 1–3.

In conclusion we have studied the sample size effect in...
pure and SiC doped MgB$_2$ samples and derived the $n$ factors for both samples. The doped samples show a larger $n$ factor and less sample size dependence, indicating a stronger pinning effect by SiC doping in MgB$_2$ samples. The irreversibility field $H_{irr}$ was found to increase with increasing sample volume as a logarithmic function. The zero-field $J_c$ decreased with decreasing sample volume as an exponential decay function.

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